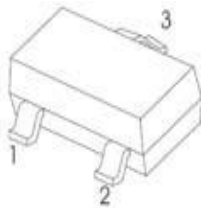
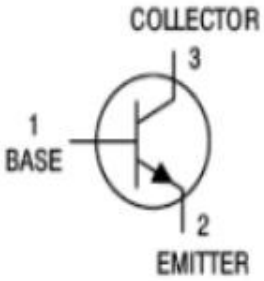
TRANSI STOR (NPN)	SOT-23 Plastic-Encapsulate Transistors

SOT-23





1.BASE
2.EMITTER
3.COLLECTOR

Marking :3D

Features

※ Complement to MMBTA94

※ High Collector-Emitter Voltage

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	400	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base Voltage	VEBO	6	V
Collector Current -Continuous	IC	200	mA
Collector Current -Puised	ICM	300	mA
Collector Power Dissipation	PC	350	mW
Thermal Resistance From Junction To Ambient	RΘJA	357	℃/W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃

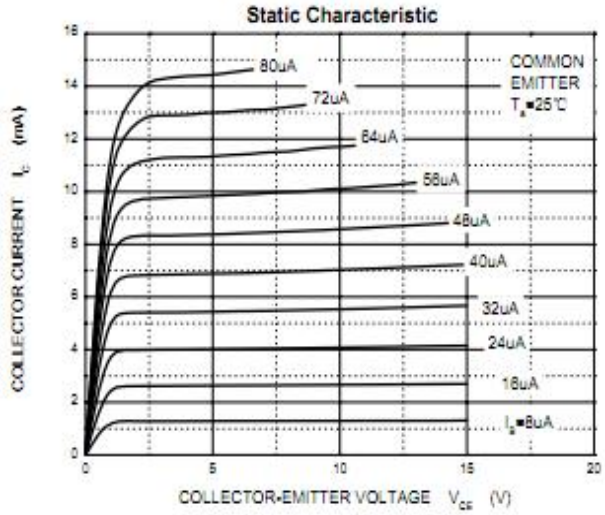
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

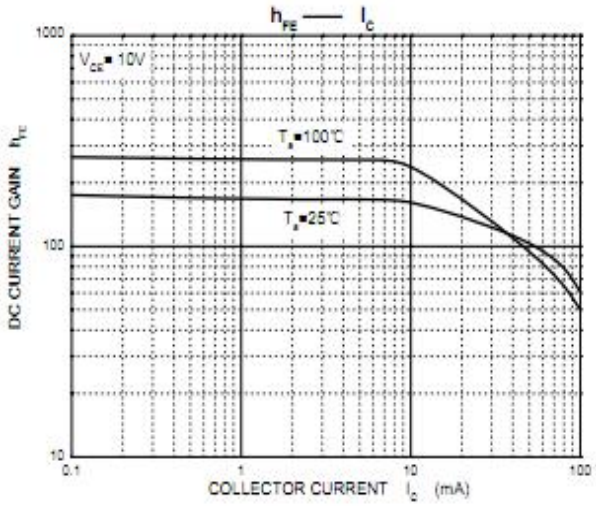
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	400		800	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	400		800	V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA, IC=0	6		30	V
Collector cut-off current	ICBO	VCB=450 V , IE=0			0.5	μA
Collector cut-off current	ICEO	VCB= 350V , IE=0			5	μA
Emitter cut-off current	IEBO	VEB= 8V , IC=0			0.3	μA
DC current gain	hFE	VCE= 10V, IC= 20mA	60			
	hFE	VCE= 10V, IC= 10mA	70		250	
Collector-emitter saturation voltage	VCE(sat)	IC= 100 mA, IB= 10mA			0.4	V
Base-emitter saturation voltage	VBE(sat)	IC= 50 mA, IB= 5mA			1	V
Transition frequency	fT	VCE= 20V, IC= 10mA f=300MHz	50			MHz
Collector output capacitance	Cob	VCB=20V, IE=0, f=1MHz			7	PF
Emitter input capacitance	Cib	VEB=0.5V, IC=0, f=1MHz			130	PF

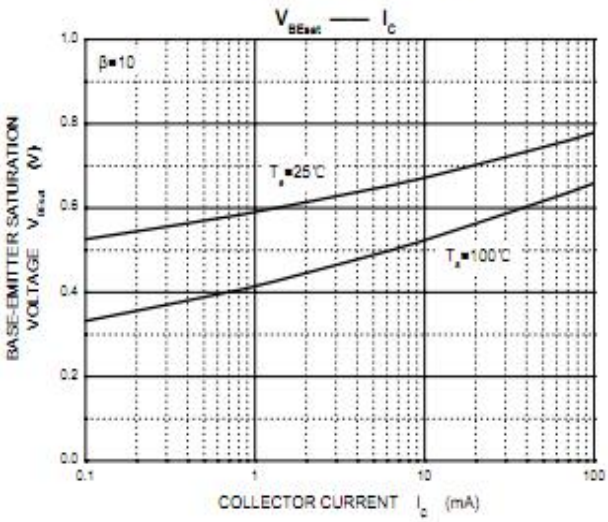
CLASSIFICATION OF hFE

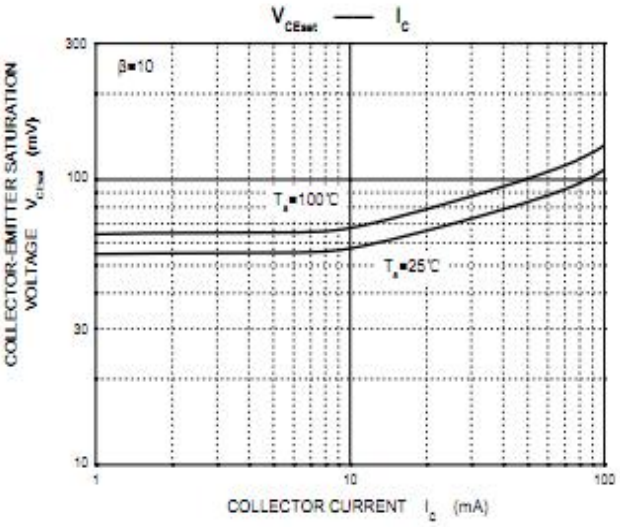
Rank	L	H	J
Range	60-100	100-200	200-250

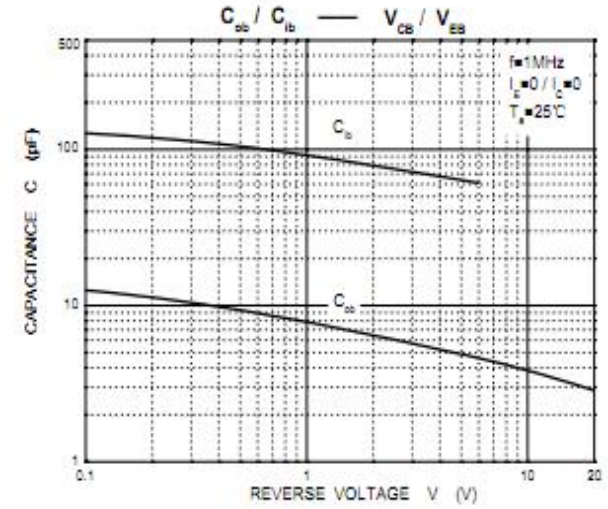
TYPICAL ELEC TRICAL AND THERMAL CHARACTERISTICS

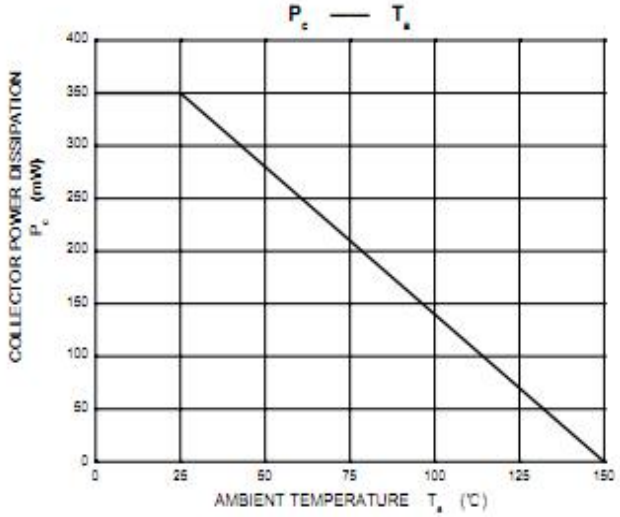












单击下面可查看定价，库存，交付和生命周期等信息

>>DIOS(迪恩思)